

SEMiX604GB126HDs



SEMiX® 4s

Trench IGBT Modules

SEMiX604GB126HDs

Features

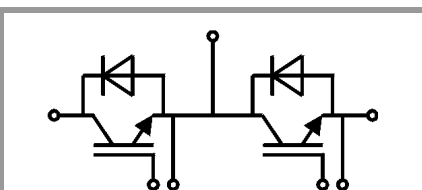
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to $T_C=125^\circ\text{C}$ max.
- Not for new design



GB

| Absolute Maximum Ratings | | | | |
|--------------------------|--|---------------------------|------------------|---------------|
| Symbol | Conditions | Values | Unit | |
| IGBT | | | | |
| V_{CES} | $T_j = 25^\circ\text{C}$ | 1200 | V | |
| I_C | $T_j = 150^\circ\text{C}$ | $T_c = 25^\circ\text{C}$ | 590 | A |
| | | $T_c = 80^\circ\text{C}$ | 413 | A |
| I_{Cnom} | | 400 | A | |
| I_{CRM} | $I_{CRM} = 2 \times I_{Cnom}$ | 800 | A | |
| V_{GES} | | -20 ... 20 | V | |
| t_{psc} | $V_{CC} = 600\text{ V}$ $V_{GE} \leq 20\text{ V}$ $V_{CES} \leq 1200\text{ V}$ | $T_j = 125^\circ\text{C}$ | 10 | μs |
| | T_j | | | |
| Inverse diode | | | | |
| I_F | $T_j = 150^\circ\text{C}$ | $T_c = 25^\circ\text{C}$ | 533 | A |
| | | $T_c = 80^\circ\text{C}$ | 367 | A |
| I_{Fnom} | | 400 | A | |
| I_{FRM} | $I_{FRM} = 2 \times I_{Fnom}$ | 800 | A | |
| I_{FSM} | $t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$ | 2500 | A | |
| T_j | | -40 ... 150 | $^\circ\text{C}$ | |
| Module | | | | |
| $I_{t(RMS)}$ | $T_{terminal} = 80^\circ\text{C}$ | 600 | A | |
| T_{stg} | | -40 ... 125 | $^\circ\text{C}$ | |
| V_{isol} | AC sinus 50Hz, t = 1 min | 4000 | V | |

| Characteristics | | | | | |
|-----------------|--|---------------------------|------|-------|------------------|
| Symbol | Conditions | min. | typ. | max. | Unit |
| IGBT | | | | | |
| $V_{CE(sat)}$ | $I_C = 400\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel | $T_j = 25^\circ\text{C}$ | 1.7 | 2.10 | V |
| | | $T_j = 125^\circ\text{C}$ | 2.0 | 2.45 | V |
| V_{CE0} | chipelevel | $T_j = 25^\circ\text{C}$ | 1 | 1.2 | V |
| | | $T_j = 125^\circ\text{C}$ | 0.9 | 1.1 | V |
| r_{CE} | $V_{GE} = 15\text{ V}$ chipelevel | $T_j = 25^\circ\text{C}$ | 1.8 | 2.3 | $\text{m}\Omega$ |
| | | $T_j = 125^\circ\text{C}$ | 2.8 | 3.4 | $\text{m}\Omega$ |
| $V_{GE(th)}$ | $V_{GE}=V_{CE}, I_C = 16\text{ mA}$ | 5 | 5.8 | 6.5 | V |
| I_{CES} | $V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$ | $T_j = 25^\circ\text{C}$ | | 5 | mA |
| | | $T_j = 125^\circ\text{C}$ | | | mA |
| C_{ies} | $V_{CE} = 25\text{ V}$ | $f = 1\text{ MHz}$ | 28.8 | | nF |
| C_{oes} | $V_{GE} = 0\text{ V}$ | $f = 1\text{ MHz}$ | 1.51 | | nF |
| C_{res} | | $f = 1\text{ MHz}$ | 1.31 | | nF |
| Q_G | $V_{GE} = -8\text{ V...} + 15\text{ V}$ | | 3200 | | nC |
| R_{Gint} | $T_j = 25^\circ\text{C}$ | | 1.88 | | Ω |
| $t_{d(on)}$ | $V_{CC} = 600\text{ V}$ $I_C = 400\text{ A}$ | $T_j = 125^\circ\text{C}$ | 330 | | ns |
| t_r | $V_{GE} = \pm 15\text{ V}$ | $T_j = 125^\circ\text{C}$ | 70 | | ns |
| E_{on} | $R_{Gon} = 2.2\ \Omega$ | $T_j = 125^\circ\text{C}$ | 36 | | mJ |
| $t_{d(off)}$ | $R_{Goff} = 2.2\ \Omega$ | $T_j = 125^\circ\text{C}$ | 630 | | ns |
| t_f | | $T_j = 125^\circ\text{C}$ | 130 | | ns |
| E_{off} | | $T_j = 125^\circ\text{C}$ | 60 | | mJ |
| $R_{th(j-c)}$ | per IGBT | | | 0.065 | K/W |

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| Characteristics | | | | | | |
|---------------------------|---|---------------------------|------|----------------|------|---------------|
| Symbol | Conditions | | min. | typ. | max. | Unit |
| Inverse diode | | | | | | |
| $V_F = V_{EC}$ | $I_F = 400\text{ A}$ $V_{GE} = 0\text{ V}$ chipllevel | $T_j = 25^\circ\text{C}$ | | 1.6 | 1.80 | V |
| | | $T_j = 125^\circ\text{C}$ | | 1.6 | 1.8 | V |
| V_{F0} | chipllevel | $T_j = 25^\circ\text{C}$ | 0.9 | 1 | 1.1 | V |
| | | $T_j = 125^\circ\text{C}$ | 0.7 | 0.8 | 0.9 | V |
| r_F | chipllevel | $T_j = 25^\circ\text{C}$ | 1.3 | 1.5 | 1.8 | m Ω |
| | | $T_j = 125^\circ\text{C}$ | 1.8 | 2.0 | 2.3 | m Ω |
| I_{RRM} | $I_F = 400\text{ A}$ | $T_j = 125^\circ\text{C}$ | | 475 | | A |
| Q_{rr} | $di/dt_{off} = 6200\text{ A}/\mu\text{s}$ | $T_j = 125^\circ\text{C}$ | | 100 | | μC |
| E_{rr} | $V_{GE} = -15\text{ V}$ $V_{CC} = 600\text{ V}$ | $T_j = 125^\circ\text{C}$ | | 46 | | mJ |
| $R_{th(j-c)}$ | per diode | | | | 0.11 | K/W |
| Module | | | | | | |
| L_{CE} | | | | 22 | | nH |
| $R_{CC'+EE'}$ | res., terminal-chip | $T_C = 25^\circ\text{C}$ | | 0.7 | | m Ω |
| | | $T_C = 125^\circ\text{C}$ | | 1 | | m Ω |
| $R_{th(c-s)}$ | per module | | | 0.03 | | K/W |
| M_s | to heat sink (M5) | | 3 | | 5 | Nm |
| M_t | | to terminals (M6) | 2.5 | | 5 | Nm |
| | | | | | | Nm |
| w | | | | | 400 | g |
| Temperature Sensor | | | | | | |
| R_{100} | $T_C=100^\circ\text{C}$ ($R_{25}=5\text{ k}\Omega$) | | | $493 \pm 5\%$ | | Ω |
| $B_{100/125}$ | $R(T)=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; $T[K]$; | | | $3550 \pm 2\%$ | | K |



GB

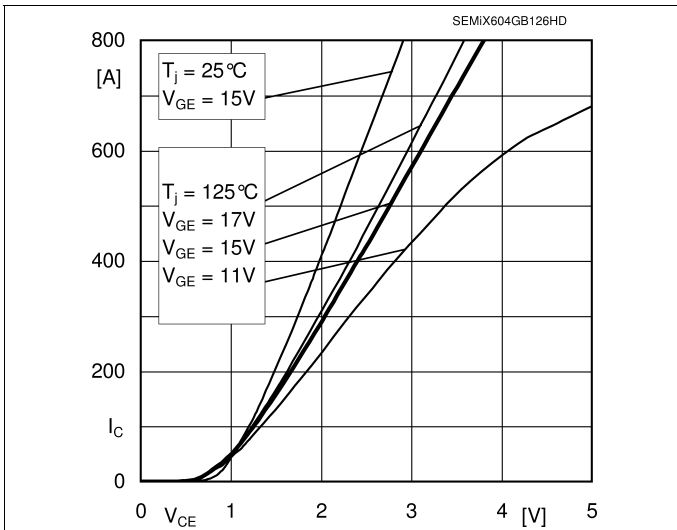


Fig. 1: Typ. output characteristic, inclusive R_{CC+EE}

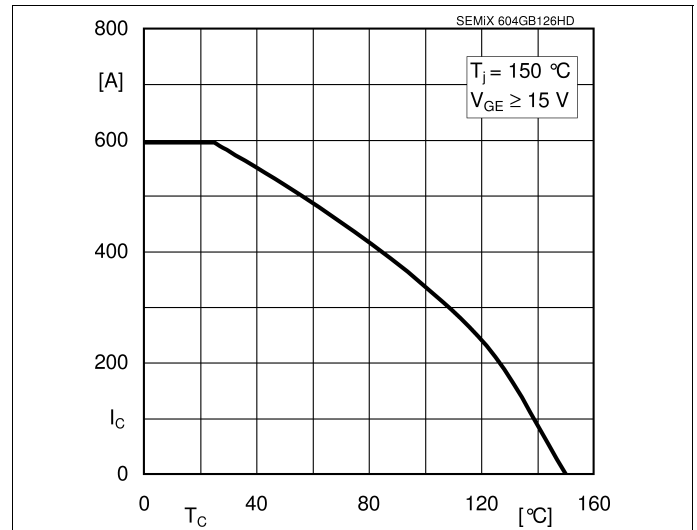


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

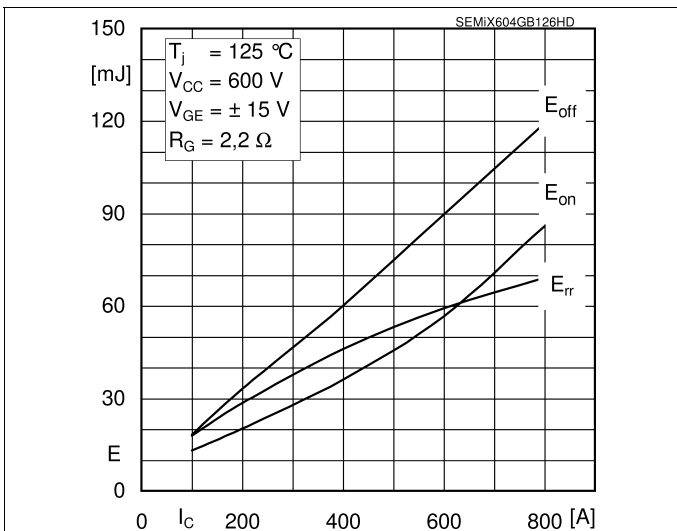


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

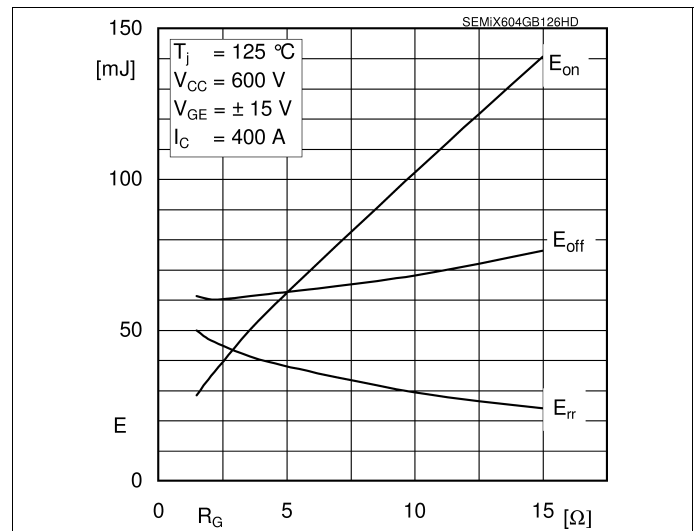


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

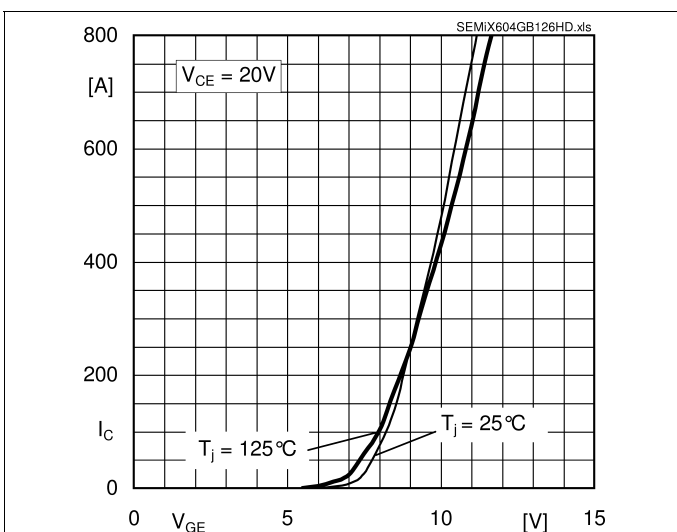


Fig. 5: Typ. transfer characteristic

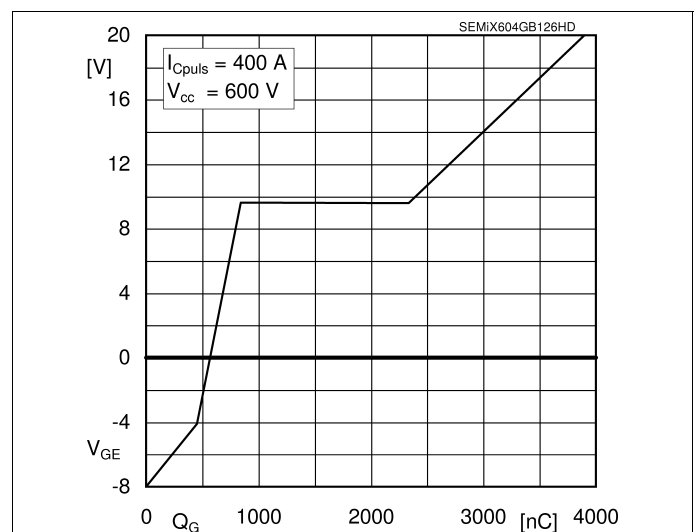


Fig. 6: Typ. gate charge characteristic

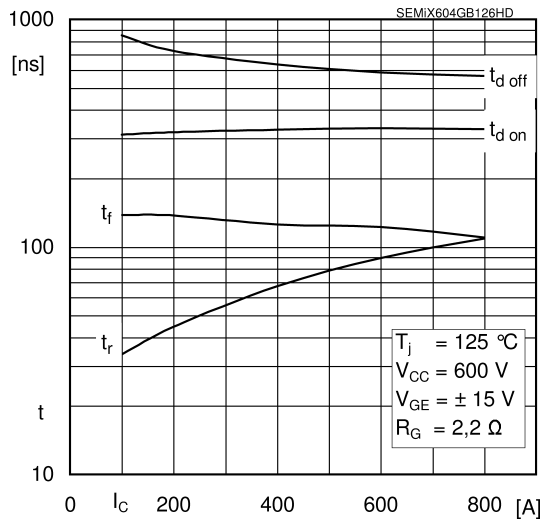


Fig. 7: Typ. switching times vs. I_C

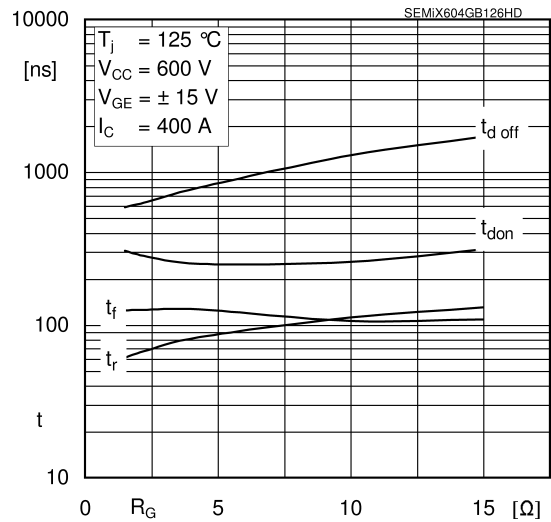


Fig. 8: Typ. switching times vs. gate resistor R_G

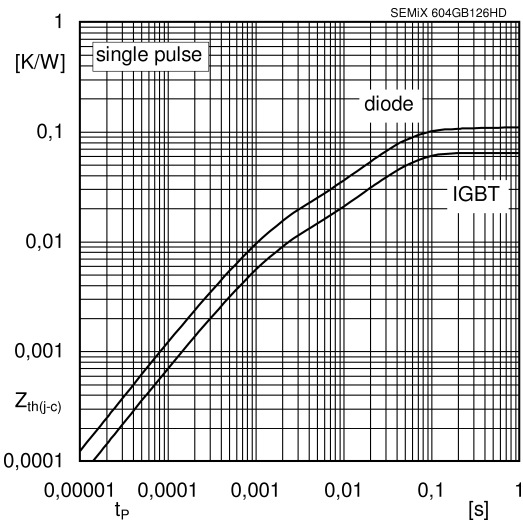


Fig. 9: Typ. transient thermal impedance

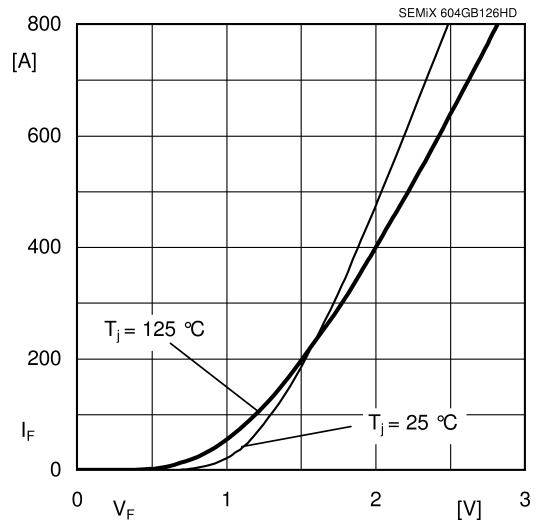


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC+EE'}$

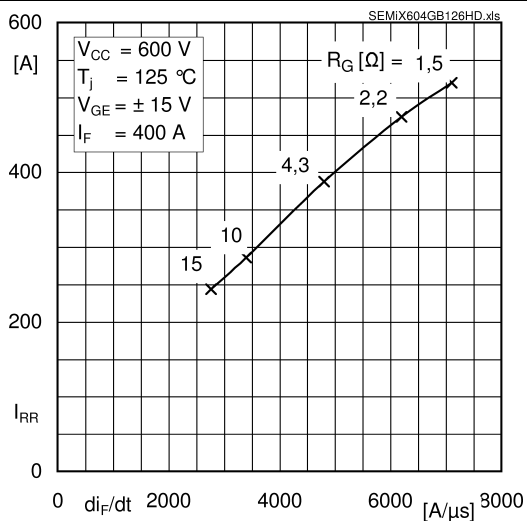


Fig. 11: Typ. CAL diode peak reverse recovery current

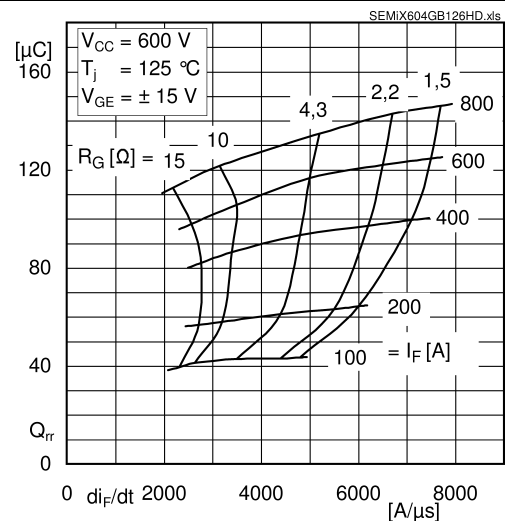
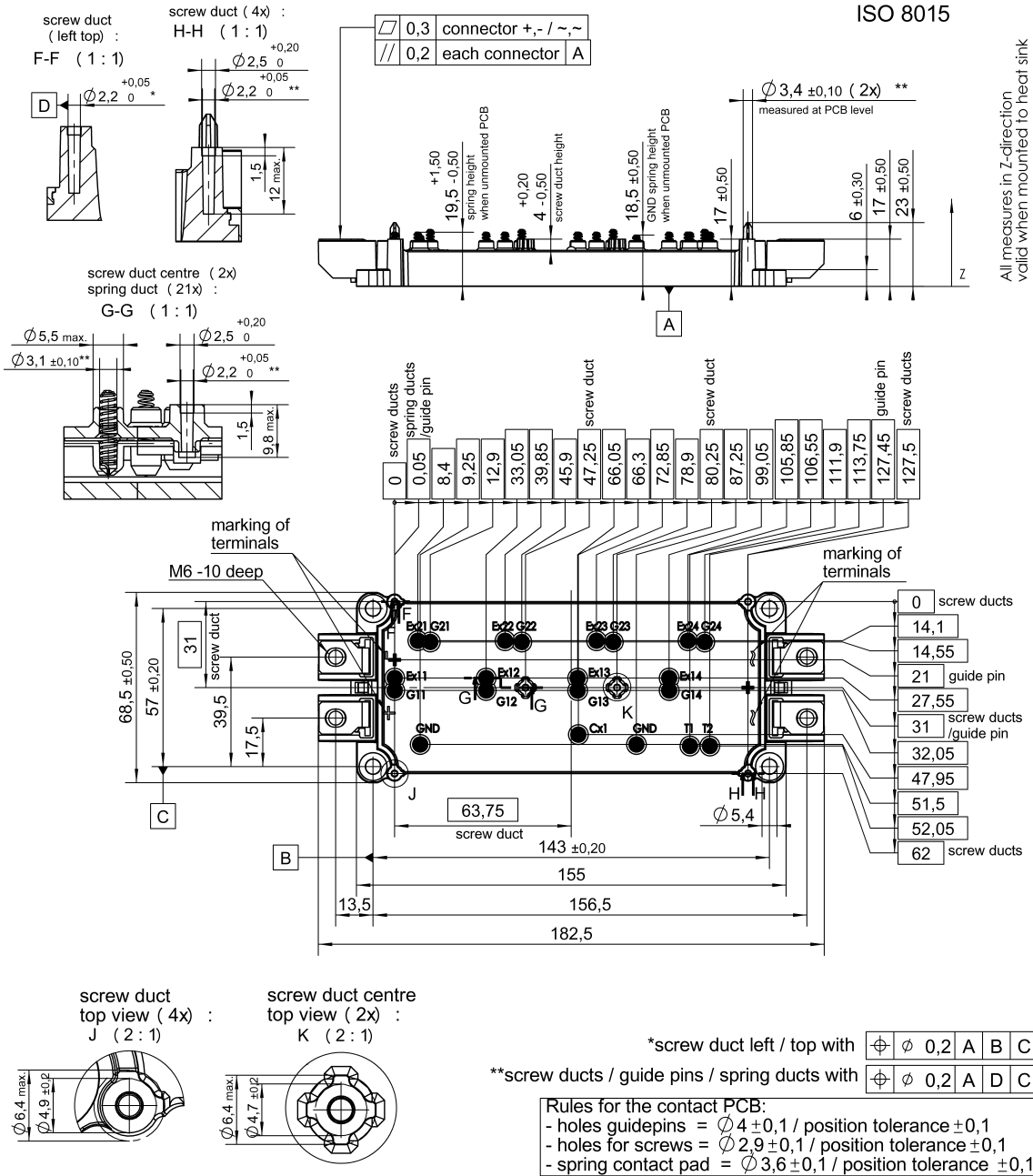


Fig. 12: Typ. CAL diode recovery charge

SEMiX604GB126HDs

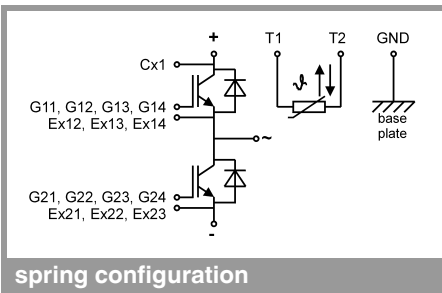
Case: SEMiX 4s

general tolerance:
ISO 2768-mK
ISO 8015



All measures in Z-direction valid when mounted to heat sink

SEMiX 4s



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.